

# High Efficiency Thyristor

$$V_{RRM} = 1200\text{ V}$$

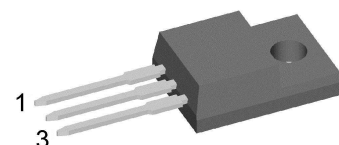
$$I_{TAV} = 10\text{ A}$$

$$V_T = 1.07\text{ V}$$

## Single Thyristor

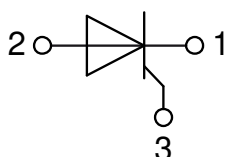
Part number

**CLA16E1200PN**



Backside: isolated

 E72873



### Features / Advantages:

- Thyristor for line frequency
- Planar passivated chip
- Long-term stability

### Applications:

- Line rectifying 50/60 Hz
- Softstart AC motor control
- DC Motor control
- Power converter
- AC power control
- Lighting and temperature control

### Package: TO-220FP

- Isolation Voltage: 2500 V~
- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0
- Soldering pins for PCB mounting
- Base plate: Plastic overmolded tab
- Reduced weight

### Disclaimer Notice

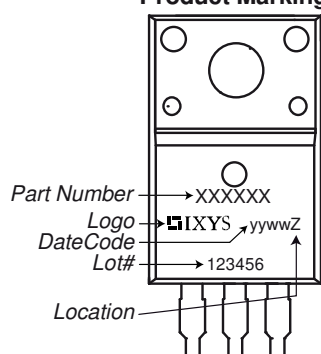
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| Thyristor      |                                                      |                                                                                                                                                                                                       |                                | Ratings |      |      |                  |
|----------------|------------------------------------------------------|-------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|--------------------------------|---------|------|------|------------------|
| Symbol         | Definition                                           | Conditions                                                                                                                                                                                            |                                | min.    | typ. | max. | Unit             |
| $V_{RSM/DSM}$  | max. non-repetitive reverse/forward blocking voltage | $T_{VJ} = 25^{\circ}\text{C}$                                                                                                                                                                         |                                |         |      | 1300 | V                |
| $V_{RRM/DRM}$  | max. repetitive reverse/forward blocking voltage     | $T_{VJ} = 25^{\circ}\text{C}$                                                                                                                                                                         |                                |         |      | 1200 | V                |
| $I_{R/D}$      | reverse current, drain current                       | $V_{R/D} = 1200\text{ V}$                                                                                                                                                                             | $T_{VJ} = 25^{\circ}\text{C}$  |         |      | 10   | $\mu\text{A}$    |
|                |                                                      | $V_{R/D} = 1200\text{ V}$                                                                                                                                                                             | $T_{VJ} = 125^{\circ}\text{C}$ |         |      | 1    | mA               |
| $V_T$          | forward voltage drop                                 | $I_T = 10\text{ A}$                                                                                                                                                                                   | $T_{VJ} = 25^{\circ}\text{C}$  |         |      | 1.14 | V                |
|                |                                                      | $I_T = 20\text{ A}$                                                                                                                                                                                   |                                |         |      | 1.32 | V                |
|                |                                                      | $I_T = 10\text{ A}$                                                                                                                                                                                   | $T_{VJ} = 125^{\circ}\text{C}$ |         |      | 1.07 | V                |
|                |                                                      | $I_T = 20\text{ A}$                                                                                                                                                                                   |                                |         |      | 1.31 | V                |
| $I_{TAV}$      | average forward current                              | $T_C = 90^{\circ}\text{C}$                                                                                                                                                                            | $T_{VJ} = 150^{\circ}\text{C}$ |         |      | 10   | A                |
| $I_{T(RMS)}$   | RMS forward current                                  | 180° sine                                                                                                                                                                                             |                                |         |      | 16   | A                |
| $V_{T0}$       | threshold voltage                                    | } for power loss calculation only                                                                                                                                                                     | $T_{VJ} = 150^{\circ}\text{C}$ |         |      | 0.81 | V                |
| $r_T$          | slope resistance                                     |                                                                                                                                                                                                       |                                |         |      | 24   | m $\Omega$       |
| $R_{thJC}$     | thermal resistance junction to case                  |                                                                                                                                                                                                       |                                |         |      | 4    | K/W              |
| $R_{thCH}$     | thermal resistance case to heatsink                  |                                                                                                                                                                                                       |                                |         | 0.5  |      | K/W              |
| $P_{tot}$      | total power dissipation                              |                                                                                                                                                                                                       | $T_C = 25^{\circ}\text{C}$     |         |      | 31   | W                |
| $I_{TSM}$      | max. forward surge current                           | $t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$                                                                                                                                                      | $T_{VJ} = 45^{\circ}\text{C}$  |         |      | 180  | A                |
|                |                                                      | $t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$                                                                                                                                                     | $V_R = 0\text{ V}$             |         |      | 195  | A                |
|                |                                                      | $t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$                                                                                                                                                      | $T_{VJ} = 150^{\circ}\text{C}$ |         |      | 155  | A                |
|                |                                                      | $t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$                                                                                                                                                     | $V_R = 0\text{ V}$             |         |      | 165  | A                |
| $I^2t$         | value for fusing                                     | $t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$                                                                                                                                                      | $T_{VJ} = 45^{\circ}\text{C}$  |         |      | 160  | A <sup>2</sup> s |
|                |                                                      | $t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$                                                                                                                                                     | $V_R = 0\text{ V}$             |         |      | 160  | A <sup>2</sup> s |
|                |                                                      | $t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$                                                                                                                                                      | $T_{VJ} = 150^{\circ}\text{C}$ |         |      | 120  | A <sup>2</sup> s |
|                |                                                      | $t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$                                                                                                                                                     | $V_R = 0\text{ V}$             |         |      | 115  | A <sup>2</sup> s |
| $C_J$          | junction capacitance                                 | $V_R = 400\text{ V}$ $f = 1\text{ MHz}$                                                                                                                                                               | $T_{VJ} = 25^{\circ}\text{C}$  |         | 7    |      | pF               |
| $P_{GM}$       | max. gate power dissipation                          | $t_p = 30\text{ }\mu\text{s}$                                                                                                                                                                         | $T_C = 150^{\circ}\text{C}$    |         |      | 5    | W                |
|                |                                                      | $t_p = 300\text{ }\mu\text{s}$                                                                                                                                                                        |                                |         |      | 2.55 | W                |
| $P_{GAV}$      | average gate power dissipation                       |                                                                                                                                                                                                       |                                |         |      | 0.5  | W                |
| $(di/dt)_{cr}$ | critical rate of rise of current                     | $T_{VJ} = 125^{\circ}\text{C}; f = 50\text{ Hz}$ repetitive, $I_T = 60\text{ A}$                                                                                                                      |                                |         |      | 150  | A/ $\mu\text{s}$ |
|                |                                                      | $t_p = 200\text{ }\mu\text{s}; di_G/dt = 0.3\text{ A}/\mu\text{s};$<br>$I_G = 0.3\text{ A}; V = \frac{2}{3} V_{DRM}$ non-repet., $I_T = 20\text{ A}$                                                  |                                |         |      | 500  | A/ $\mu\text{s}$ |
| $(dv/dt)_{cr}$ | critical rate of rise of voltage                     | $V = \frac{2}{3} V_{DRM}$                                                                                                                                                                             | $T_{VJ} = 125^{\circ}\text{C}$ |         |      | 500  | V/ $\mu\text{s}$ |
|                |                                                      | $R_{GK} = \infty$ ; method 1 (linear voltage rise)                                                                                                                                                    |                                |         |      |      |                  |
| $V_{GT}$       | gate trigger voltage                                 | $V_D = 6\text{ V}$                                                                                                                                                                                    | $T_{VJ} = 25^{\circ}\text{C}$  |         |      | 1.3  | V                |
|                |                                                      |                                                                                                                                                                                                       | $T_{VJ} = -40^{\circ}\text{C}$ |         |      | 1.6  | V                |
| $I_{GT}$       | gate trigger current                                 | $V_D = 6\text{ V}$                                                                                                                                                                                    | $T_{VJ} = 25^{\circ}\text{C}$  |         |      | 30   | mA               |
|                |                                                      |                                                                                                                                                                                                       | $T_{VJ} = -40^{\circ}\text{C}$ |         |      | 50   | mA               |
| $V_{GD}$       | gate non-trigger voltage                             | $V_D = \frac{2}{3} V_{DRM}$                                                                                                                                                                           | $T_{VJ} = 150^{\circ}\text{C}$ |         |      | 0.2  | V                |
| $I_{GD}$       | gate non-trigger current                             |                                                                                                                                                                                                       |                                |         |      | 1    | mA               |
| $I_L$          | latching current                                     | $t_p = 10\text{ }\mu\text{s}$                                                                                                                                                                         | $T_{VJ} = 25^{\circ}\text{C}$  |         |      | 60   | mA               |
|                |                                                      | $I_G = 0.3\text{ A}; di_G/dt = 0.3\text{ A}/\mu\text{s}$                                                                                                                                              |                                |         |      |      |                  |
| $I_H$          | holding current                                      | $V_D = 6\text{ V}$ $R_{GK} = \infty$                                                                                                                                                                  | $T_{VJ} = 25^{\circ}\text{C}$  |         |      | 60   | mA               |
| $t_{gd}$       | gate controlled delay time                           | $V_D = \frac{1}{2} V_{DRM}$                                                                                                                                                                           | $T_{VJ} = 25^{\circ}\text{C}$  |         |      | 2    | $\mu\text{s}$    |
|                |                                                      | $I_G = 0.3\text{ A}; di_G/dt = 0.3\text{ A}/\mu\text{s}$                                                                                                                                              |                                |         |      |      |                  |
| $t_q$          | turn-off time                                        | $V_R = 100\text{ V}; I_T = 20\text{ A}; V = \frac{2}{3} V_{DRM}$ $T_{VJ} = 125^{\circ}\text{C}$<br>$di/dt = 10\text{ A}/\mu\text{s}$ $dv/dt = 20\text{ V}/\mu\text{s}$ $t_p = 200\text{ }\mu\text{s}$ |                                |         | 150  |      | $\mu\text{s}$    |

| Package TO-220FP |                                                              |                      |                                     | Ratings |      |      |      |
|------------------|--------------------------------------------------------------|----------------------|-------------------------------------|---------|------|------|------|
| Symbol           | Definition                                                   | Conditions           |                                     | min.    | typ. | max. | Unit |
| $I_{RMS}$        | RMS current                                                  | per terminal         |                                     |         |      | 35   | A    |
| $T_{VJ}$         | virtual junction temperature                                 |                      |                                     | -55     |      | 150  | °C   |
| $T_{op}$         | operation temperature                                        |                      |                                     | -55     |      | 125  | °C   |
| $T_{stg}$        | storage temperature                                          |                      |                                     | -55     |      | 150  | °C   |
| <b>Weight</b>    |                                                              |                      |                                     |         | 2    |      | g    |
| $M_D$            | mounting torque                                              |                      |                                     | 0.4     |      | 0.6  | Nm   |
| $F_C$            | mounting force with clip                                     |                      |                                     | 20      |      | 60   | N    |
| $d_{Spp/App}$    | creepage distance on surface   striking distance through air | terminal to terminal | 1.6                                 | 1.0     |      |      | mm   |
| $d_{Spb/Apb}$    |                                                              | terminal to backside | 2.5                                 | 2.5     |      |      | mm   |
| $V_{ISOL}$       | isolation voltage                                            | t = 1 second         | 50/60 Hz, RMS; $I_{ISOL} \leq 1$ mA | 2500    |      |      | V    |
|                  |                                                              | t = 1 minute         |                                     | 2100    |      |      | V    |

### Product Marking



### Part description

C = Thyristor (SCR)  
 L = High Efficiency Thyristor  
 A = (up to 1200V)  
 16 = Current Rating [A]  
 E = Single Thyristor  
 1200 = Reverse Voltage [V]  
 PN = TO-220ABFP (3)

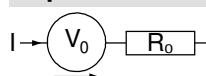
| Ordering | Ordering Number | Marking on Product | Delivery Mode | Quantity | Code No. |
|----------|-----------------|--------------------|---------------|----------|----------|
| Standard | CLA16E1200PN    | CLA16E1200PN       | Tube          | 50       | 517734   |

| Similar Part | Package        | Voltage class |
|--------------|----------------|---------------|
| CLA16E800PN  | TO-220ABFP (3) | 800           |
| CS22-12io1M  | TO-220ABFP (3) | 1200          |
| CS22-08io1M  | TO-220ABFP (3) | 800           |
| CMA30E1600PN | TO-220ABFP (3) | 1600          |

### Equivalent Circuits for Simulation

\* on die level

$T_{VJ} = 150^{\circ}\text{C}$



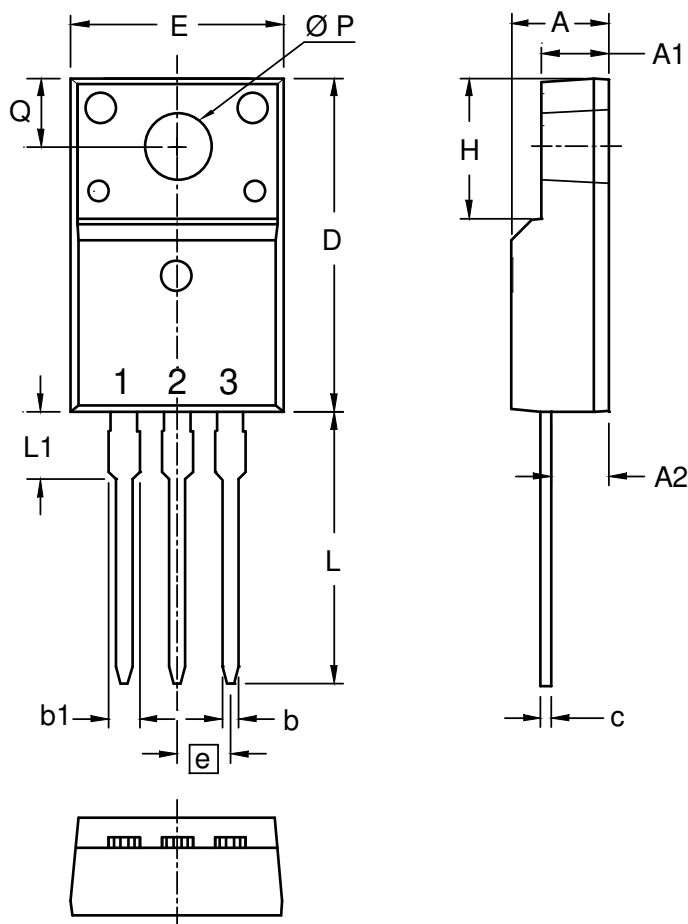
Thyristor

$V_{0\max}$  threshold voltage 0.81

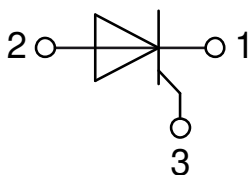
$R_{0\max}$  slope resistance \* 21

V

mΩ

**Outlines TO-220FP**


| Dim. | Millimeters |       | Inches    |       |
|------|-------------|-------|-----------|-------|
|      | min         | max   | min       | max   |
| A    | 4.50        | 4.90  | 0.177     | 0.193 |
| A1   | 2.34        | 2.74  | 0.092     | 0.108 |
| A2   | 2.56        | 2.96  | 0.101     | 0.117 |
| b    | 0.70        | 0.90  | 0.028     | 0.035 |
| c    | 0.45        | 0.60  | 0.018     | 0.024 |
| D    | 15.67       | 16.07 | 0.617     | 0.633 |
| E    | 9.96        | 10.36 | 0.392     | 0.408 |
| e    | 2.54 BSC    |       | 0.100 BSC |       |
| H    | 6.48        | 6.88  | 0.255     | 0.271 |
| L    | 12.68       | 13.28 | 0.499     | 0.523 |
| L1   | 3.03        | 3.43  | 0.119     | 0.135 |
| ØP   | 3.08        | 3.28  | 0.121     | 0.129 |
| Q    | 3.20        | 3.40  | 0.126     | 0.134 |



## Thyristor

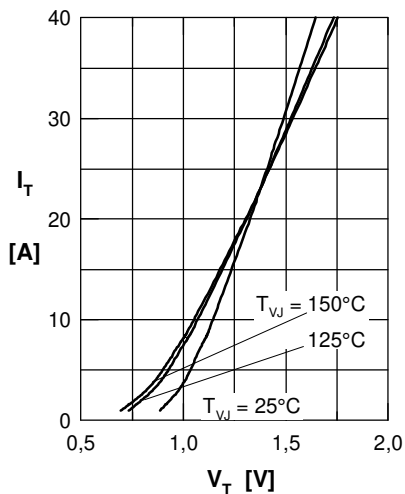


Fig. 1 Forward characteristics

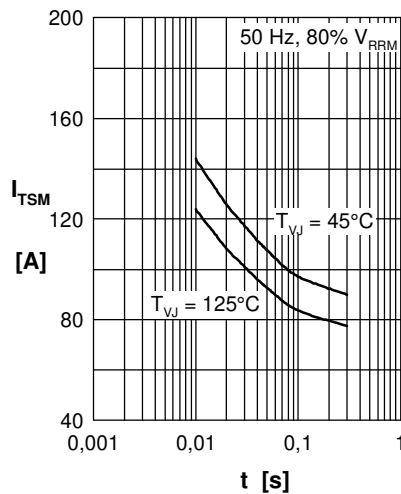


Fig. 2 Surge overload current  
 $I_{TSM}$ : crest value,  $t$ : duration

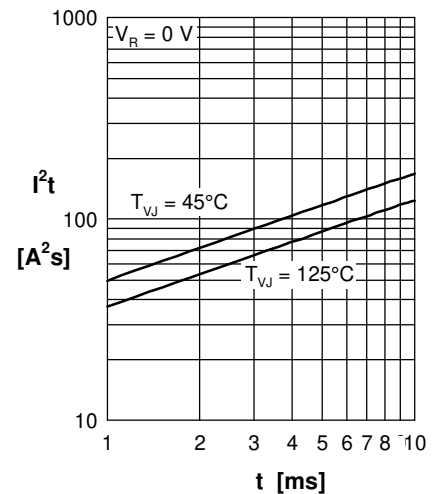


Fig. 3  $I^2t$  versus time (1-10 s)

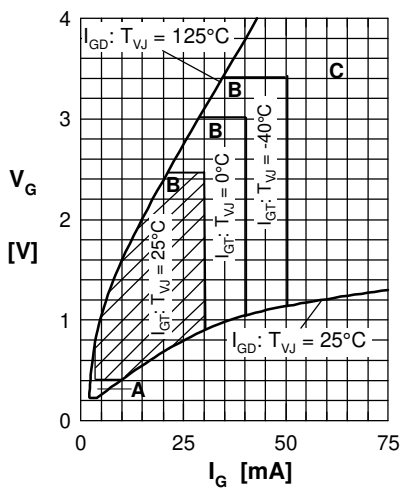


Fig. 4 Gate voltage & gate current  
Triggering: A = no; B = possible; C = safe

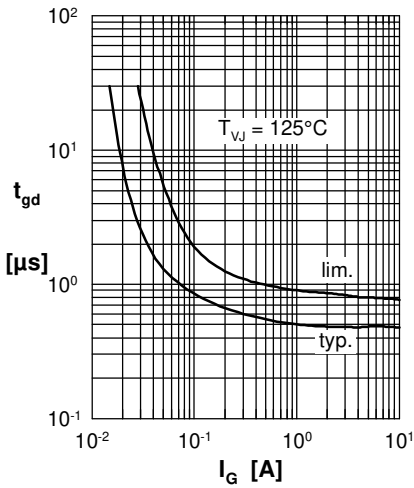


Fig. 5 Gate controlled delay time  $t_{gd}$

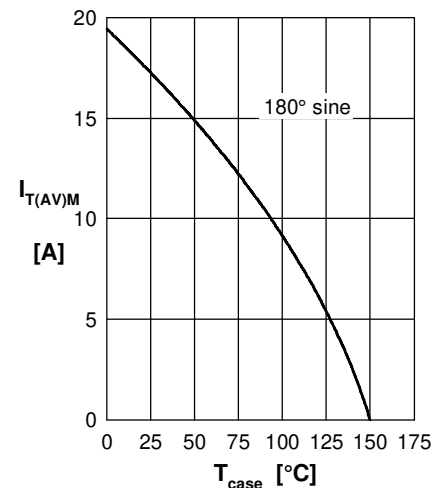


Fig. 6 Max. forward current at case temperature

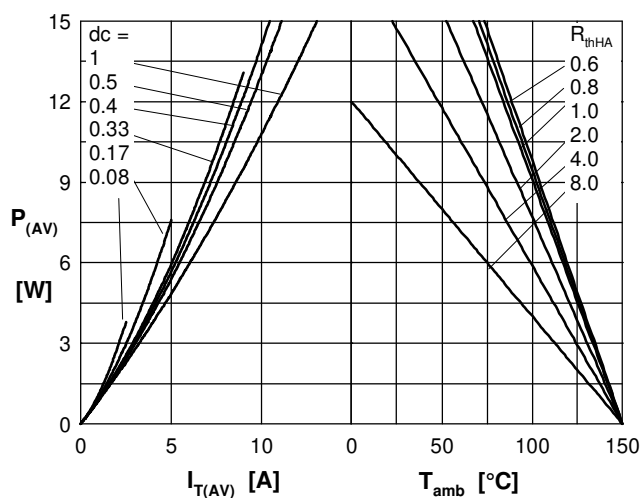


Fig. 7a Power dissipation versus direct output current  
Fig. 7b and ambient temperature

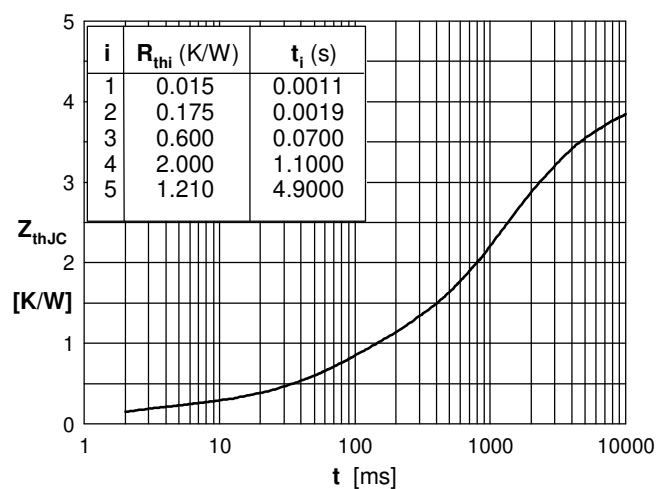


Fig. 8 Transient thermal impedance junction to case

